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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	97
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p250-1fg144t

Table 2-3 • **Overshoot and Undershoot Limits (as measured on quiet I/Os)**

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle	Maximum Overshoot/ Undershoot (115°C)	Maximum Overshoot/ Undershoot (135°C)
2.7 V or less	10%	0.81 V	0.72 V
	5%	0.90 V	0.82 V
3 V	10%	0.80 V	0.72 V
	5%	0.90 V	0.81 V
3.3 V	10%	0.79 V	0.69 V
	5%	0.88 V	0.79 V
3.6 V	10%	N/A	N/A
	5%	N/A	N/A

Notes:

1. *The duration is allowed at one out of six clock cycles (estimated SSO density over cycles). If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
2. *This table refers only to overshoot/undershoot limits for simultaneously switching I/Os and does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-2 on page 2-4.

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-2 on page 2-4).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI T**rip Point:**
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC **Trip Point:**
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to V_{CCI}.
- JTAG supply, PLL power supplies, and charge pump V_{PUMP} supply have no influence on I/O behavior.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

Table 2-8 • **Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings [1] Applicable to Standard Plus I/O Banks**

	VMV (V)	Static Power PDC2 (mW)[1]	Dynamic Power PAC9 (µW/MHz)[2]
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	3.3	–	16.72
2.5 V LVCMOS	2.5	–	5.14
1.8 V LVCMOS	1.8	–	2.13
1.5 V LVCMOS (JESD8-11)	1.5	–	1.48
3.3 V PCI	3.3	–	18.13
3.3 V PCI-X	3.3	–	18.13

Notes:

1. *P_{DC2} is the static power (where applicable) measured on VMV.*
2. *P_{AC9} is the total dynamic power measured on V_{CC} and VMV.*

Table 2-9 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings [1] Applicable to Advanced I/O Banks**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	468.67
2.5 V LVCMOS	35	2.5	–	267.48
1.8 V LVCMOS	35	1.8	–	149.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	103.12
3.3 V PCI	10	3.3	–	201.02
3.3 V PCI-X	10	3.3	–	201.02
Differential				
LVDS	–	2.5	7.74	88.92
LVPECL	–	3.3	19.54	166.52

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *P_{DC3} is the static power (where applicable) measured on VMV.*
3. *P_{AC10} is the total dynamic power measured on V_{CCI} and VMV.*

Table 2-13 • **Enable Rate Guidelines Recommended for Power Calculation**

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

User I/O Characteristics

Timing Model

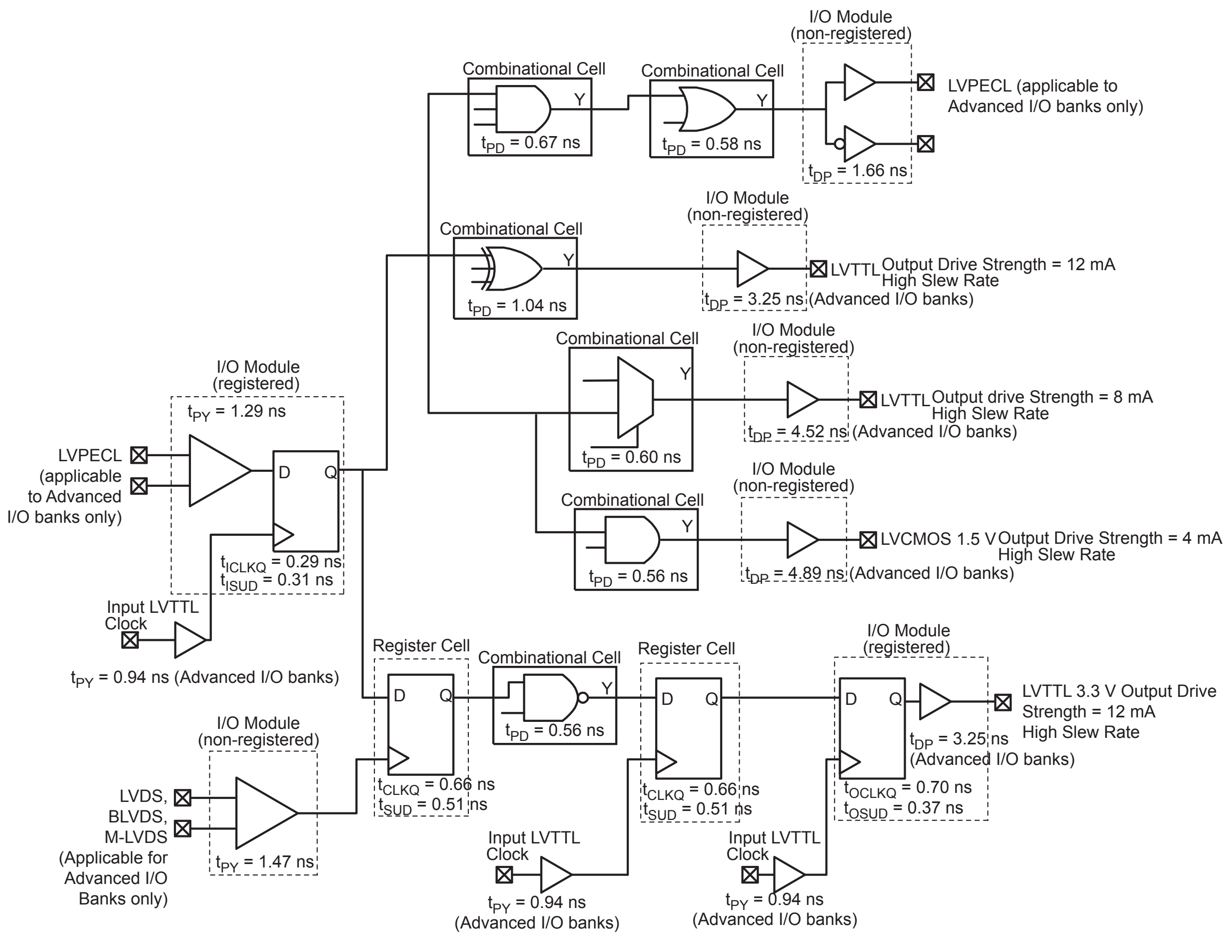


Figure 2-3 • **Timing Model**
Operating Conditions: –1 Speed, Automotive Grade 2 Temp. Range (T_J = 115°C), Worst Case VCC = 1.425 V

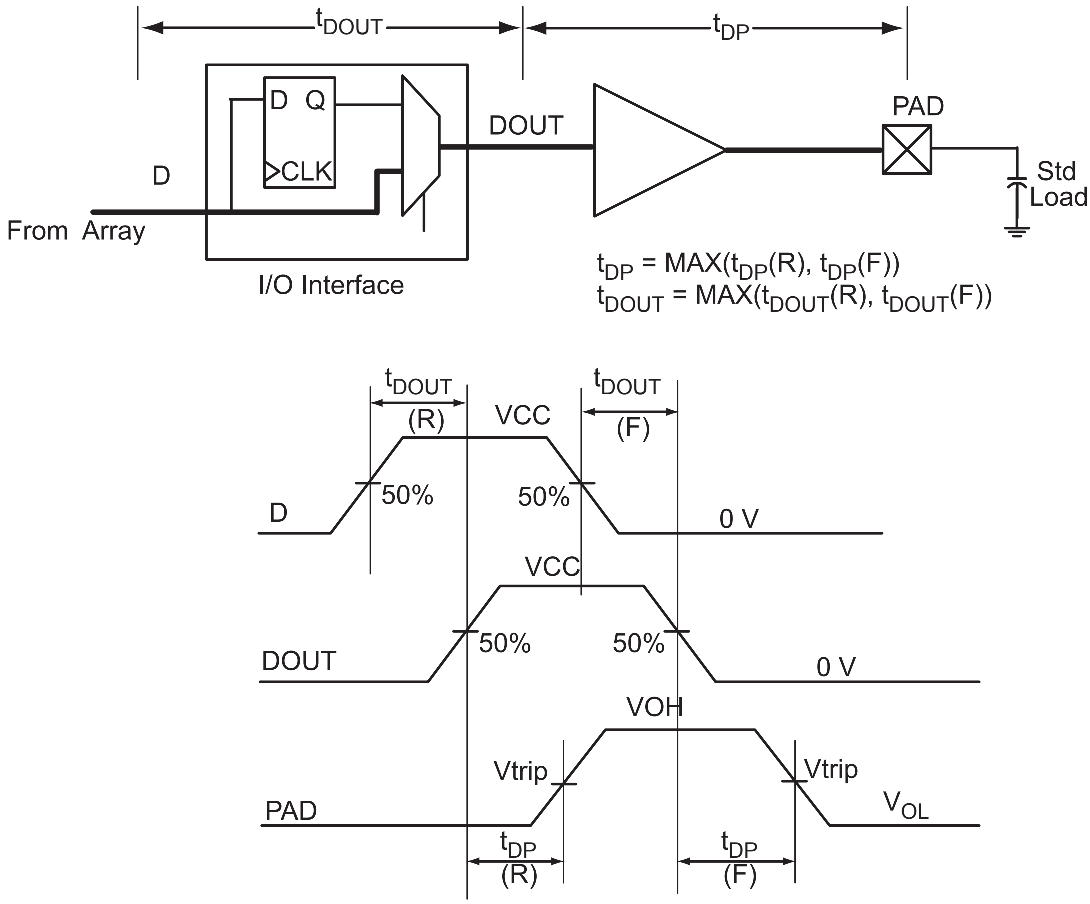


Figure 2-5 • **Output Buffer Model and Delays (example)**

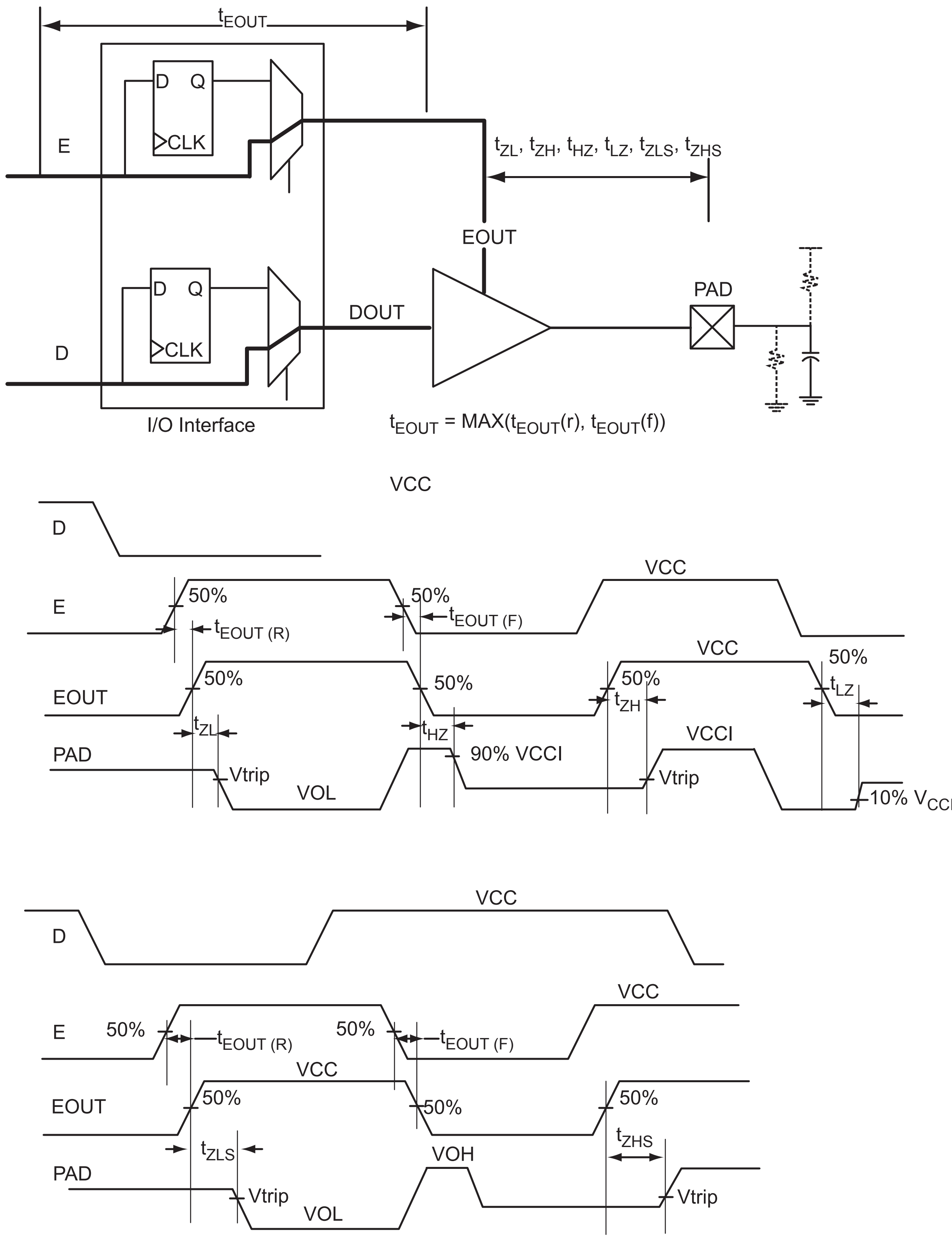


Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (example)**

Table 2-23 • Summary of I/O Timing Characteristics—Software Default Settings –1 Speed Grade, Automotive-Case Conditions: T_J = 115°C, Worst Case VCC = 1.425 V Worst Case VCCI = 3.0 V Standard Plus I/O Banks

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.55	3.36	0.04	0.97	0.39	3.42	1.56	3.05	1.94	5.55	2.80	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.55	3.05	0.04	1.23	0.39	3.11	2.99	1.56	1.69	5.23	5.11	ns
1.8 V LVCMOS	8 mA	High	35 pF	–	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.99	ns
1.5 V LVCMOS	4 mA	High	35 pF	–	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.18	ns
3.3 V PCI	Per PCI spec	High	10 pF	25 [2]	0.55	2.55	0.04	0.82	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25 [2]	0.55	2.55	0.04	0.79	0.39	1.27	0.94	2.65	3.06	2.49	2.18	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*
2. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-11 on page 2-48 for connectivity. This resistor is not required during normal operation.*

Detailed I/O DC Characteristics

Table 2-24 • **Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	VIN = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz		8	pF

Table 2-25 • **I/O Output Buffer Maximum Resistances[1] Applicable to Advanced I/O Banks**

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	6 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on V_{CCI}, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. *$R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / I_{OLspec}*
3. *$R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / I_{OHspec}*

Table 2-29 • **I/O Short Currents IOSH/IOSL Applicable to Standard Plus I/O Banks**

	Drive Strength	I_{OSL} (mA)*	I_{OSH} (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	109	103
2.5 V LVCMOS	2 mA	18	16
	6 mA	37	32
	12 mA	74	65
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	44	35
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

Note: *T_J = 100°C*

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 110°C, the short current condition would have to be sustained for more than three months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-30 • **Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months
110°C	3 months
125°C	25 days
135°	12 days

Table 2-52 • 2.5 V LVCMOS High Slew
Automotive-Case Conditions: TJ = 115°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	8.95	0.05	1.40	0.45	8.01	8.95	1.20	1.09	10.43	11.37	ns
	-1	0.53	7.62	0.04	1.19	0.38	6.82	7.62	1.20	1.09	8.87	9.68	ns
6 mA	STD	0.63	5.25	0.05	1.40	0.45	5.03	5.25	1.38	1.42	7.44	7.67	ns
	-1	0.53	4.47	0.04	1.19	0.38	4.27	4.47	1.38	1.42	6.33	6.52	ns
12 mA	STD	0.63	3.47	0.05	1.40	0.45	3.53	3.40	1.51	1.63	5.95	5.82	ns
	-1	0.53	2.95	0.04	1.19	0.38	3.01	2.89	1.51	1.63	5.06	4.95	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.*

Table 2-53 • 2.5 V LVCMOS Low Slew
Automotive-Case Conditions: T_J = 115°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	11.73	0.05	1.40	0.45	11.51	11.73	1.21	1.04	13.93	14.15	ns
	-1	0.53	9.98	0.04	1.19	0.38	9.79	9.98	1.21	1.04	11.85	12.03	ns
6 mA	STD	0.63	7.97	0.05	1.40	0.45	8.12	7.96	1.38	1.37	10.54	10.38	ns
	-1	0.53	6.78	0.04	1.19	0.38	6.91	6.77	1.39	1.37	8.96	8.83	ns
12 mA	STD	0.63	6.09	0.05	1.40	0.45	6.20	5.96	1.51	1.58	8.62	8.38	ns
	-1	0.53	5.18	0.04	1.19	0.38	5.28	5.07	1.51	1.58	7.33	7.12	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-80 • 3.3 V PCI/PCI-X
Automotive-Case Conditions: T_J = 115°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.628	2.50	0.05	0.92	0.45	1.23	0.91	3.02	3.48	2.40	2.11	ns
–1	0.53	2.12	0.04	0.78	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-81 • 3.3 V PCI/PCI-X
Automotive-Case Conditions: T_J = 115°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.628	2.90	0.05	0.90	0.45	1.23	0.91	3.02	3.48	2.40	2.11	ns
–1	0.53	2.47	0.04	0.77	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Differential I/O Characteristics

Physical Implementation

Configuration of the I/O modules as a differential pair is handled by Actel Designer software when the user instantiates a differential I/O macro in the design.

Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and Double Data Rate (DDR). However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-12 on page 2-50. The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, ProASIC3 also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).

Output Enable Register

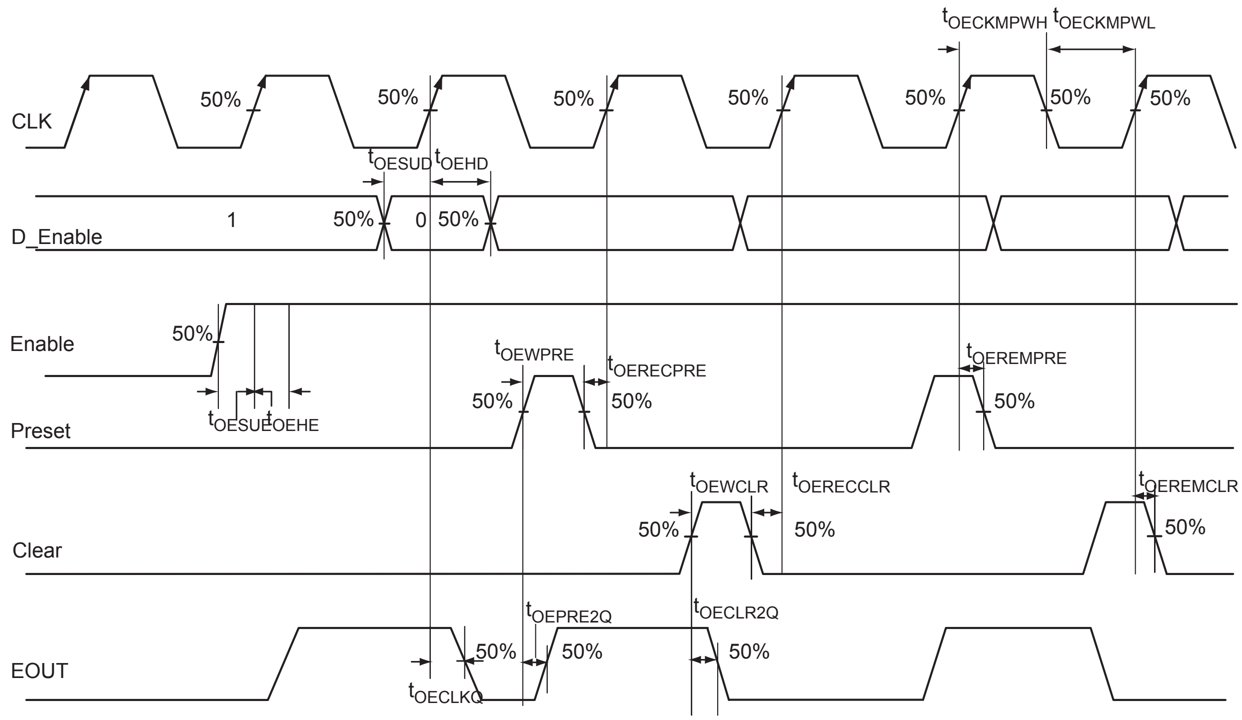


Figure 2-19 • Output Enable Register Timing Diagram

Timing Characteristics

Table 2-96 • Output Enable Register Propagation Delays
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.54	0.64	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.38	0.45	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.53	0.62	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.81	0.95	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.81	0.95	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.27	0.32	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.27	0.32	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

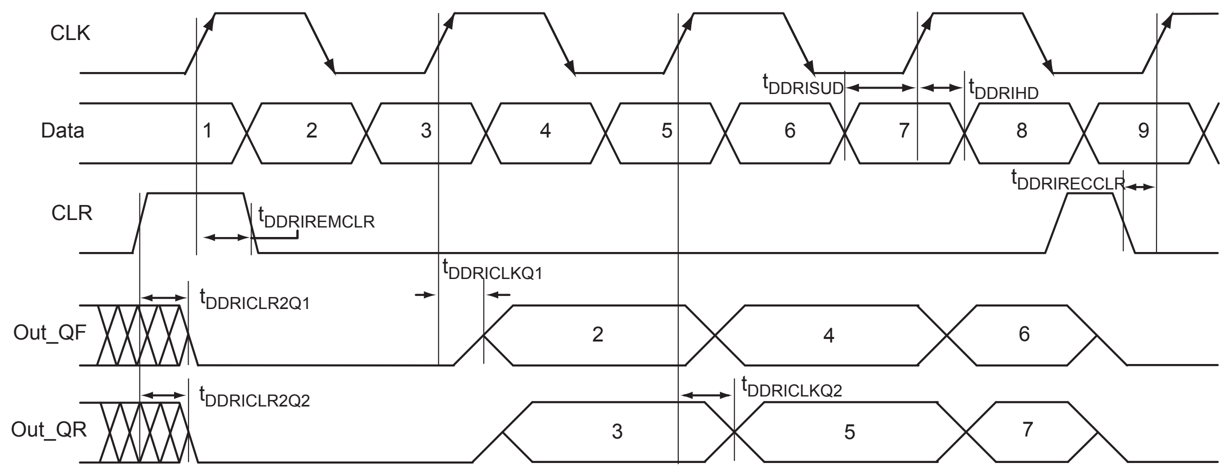


Figure 2-21 • **Input DDR Timing Diagram**

Timing Characteristics

Table 2-99 • **Input DDR Propagation Delays**
Automotive-Case Conditions: TJ = 135°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.33	0.39	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.47	0.56	ns
$t_{DDRISUD}$	Data Setup for Input DDR	0.34	0.40	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.56	0.66	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.69	0.82	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.27	0.32	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.25	0.30	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.41	0.48	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.37	0.43	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to *Table 2-5 on page 2-5* *for derating values.*

Output DDR Module

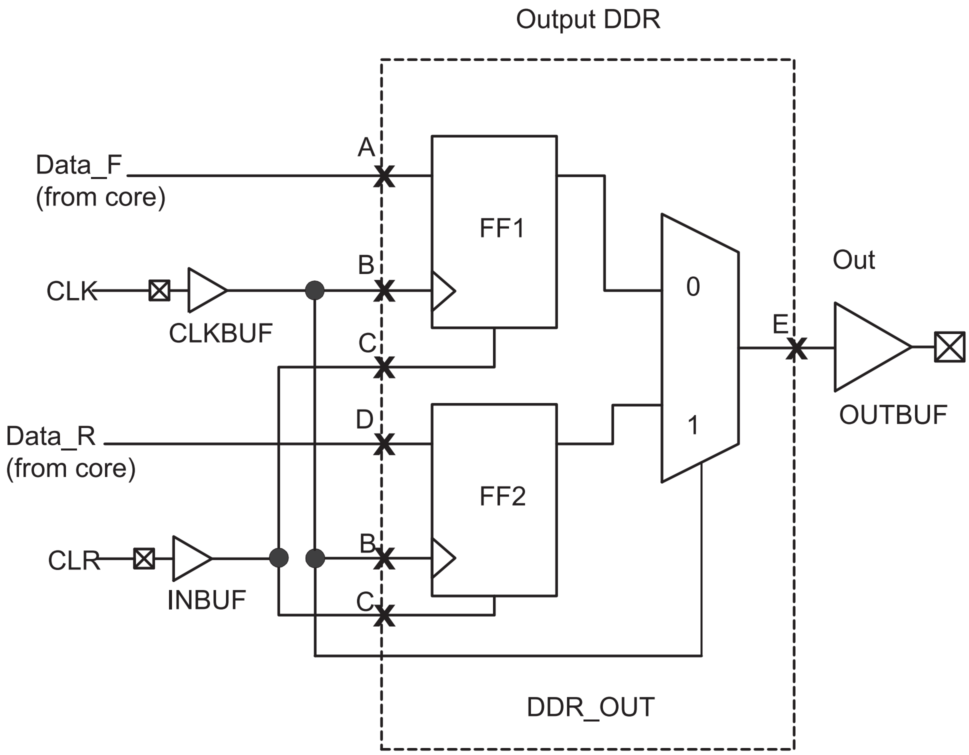


***Figure 2-22* • Output DDR Timing Model**

***Table 2-101* • Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

FIFO

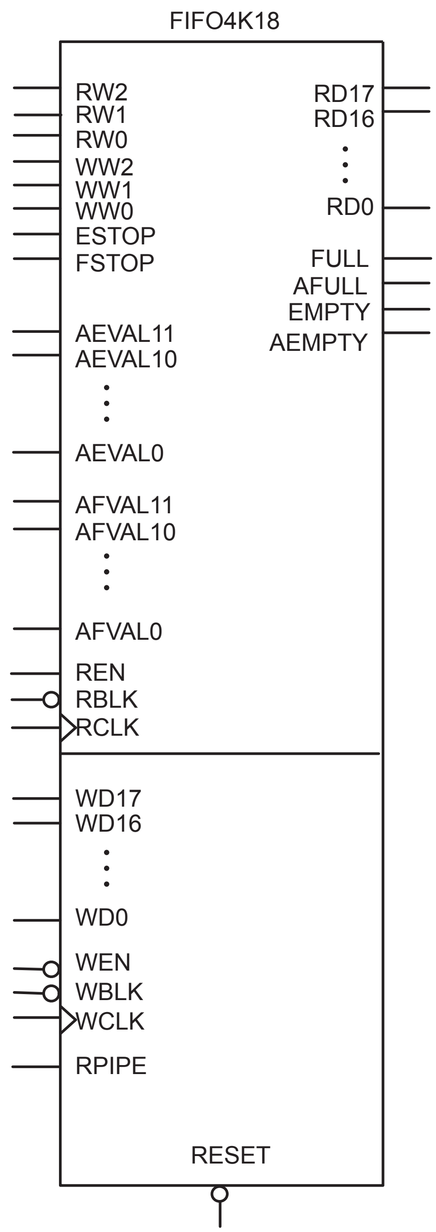


Figure 2-36 **• FIFO Model**

Table 2-122 **• FIFO**
Worst-Case Automotive Conditions: T_J = 115°C, VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.93	1.64	ns
t_{ENH}	REN, WEN Hold Time	0.03	0.02	ns
t_{BKS}	BLK Setup Time	0.27	0.32	ns
t_{BKH}	BLK Hold Time	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.26	0.22	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.30	2.81	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.25	1.07	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.41	2.05	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.29	1.95	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	8.68	7.38	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.37	2.02	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	8.59	7.30	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.29	1.10	ns
	RESET Low to Data Out Low on RD (pipelined)	1.29	1.10	ns
$t_{REMRSTB}$	RESET Removal	0.40	0.34	ns
$t_{RECRSTB}$	RESET Recovery	2.10	1.79	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.30	0.25	ns
t_{CYC}	Clock Cycle Time	4.53	3.85	ns
F_{MAX}	Maximum Frequency for FIFO	221	260	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Embedded FlashROM Characteristics

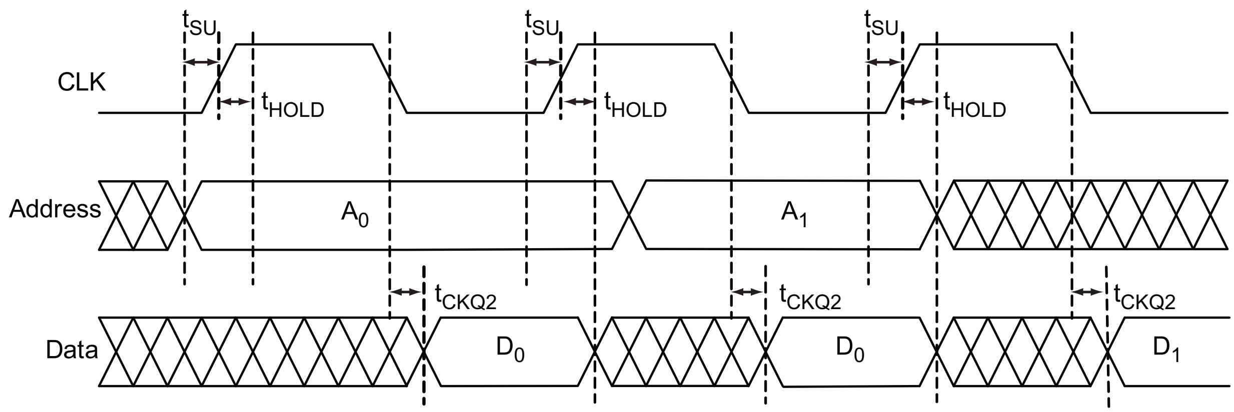


***Figure 2-44* • Timing Diagram**

Timing Characteristics

***Table 2-123* • Embedded FlashROM Access Time**
Automotive-Case Conditions: T_J = 135°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{SU}	Address Setup Time	0.65	0.76	ns
t_{HOLD}	Address Hold Time	0.00	0.00	ns
t_{CK2Q}	Clock to Out	19.73	23.20	ns
F_{MAX}	Maximum Clock Frequency	15	15	MHz

***Table 2-124* • Embedded FlashROM Access Time**
Automotive-Case Conditions: T_J = 115°C, Worst-Case VCC = 1.425 V

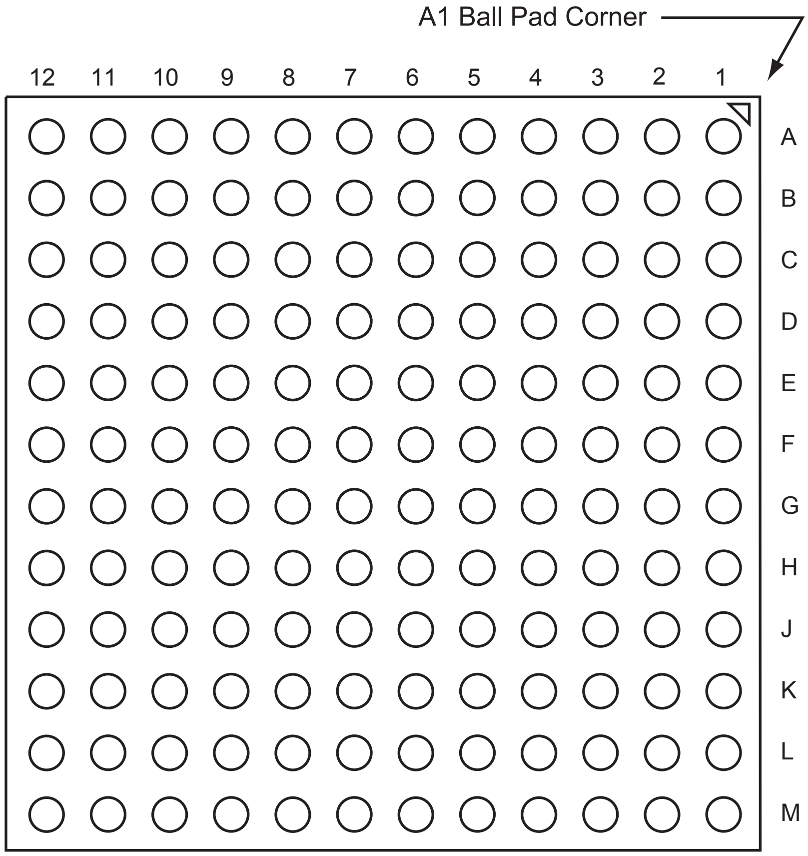
Parameter	Description	–1	Std.	Units
t_{SU}	Address Setup Time	0.64	0.75	ns
t_{HOLD}	Address Hold Time	0.00	0.00	ns
t_{CK2Q}	Clock to Out	19.35	22.74	ns
F_{MAX}	Maximum Clock Frequency	15	15	MHz

QN132	
Pin Number	A3P125 Function
A1	GAB2/IO69RSB1
A2	IO130RSB1
A3	VCCIB1
A4	GFC1/IO126RSB1
A5	GFB0/IO123RSB1
A6	VCCPLF
A7	GFA1/IO121RSB1
A8	GFC2/IO118RSB1
A9	IO115RSB1
A10	VCC
A11	GEB1/IO110RSB1
A12	GEA0/IO107RSB1
A13	GEC2/IO104RSB1
A14	IO100RSB1
A15	VCC
A16	IO99RSB1
A17	IO96RSB1
A18	IO94RSB1
A19	IO91RSB1
A20	IO85RSB1
A21	IO79RSB1
A22	VCC
A23	GDB2/IO71RSB1
A24	TDI
A25	TRST
A26	GDC1/IO61RSB0
A27	VCC
A28	IO60RSB0
A29	GCC2/IO59RSB0
A30	GCA2/IO57RSB0
A31	GCA0/IO56RSB0
A32	GCB1/IO53RSB0
A33	IO49RSB0
A34	VCC
A35	IO44RSB0
A36	GBA2/IO41RSB0

QN132	
Pin Number	A3P125 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO68RSB1
B2	GAC2/IO131RSB1
B3	GND
B4	GFC0/IO125RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO119RSB1
B8	IO116RSB1
B9	GND
B10	GEB0/IO109RSB1
B11	VMV1
B12	GEB2/IO105RSB1
B13	IO101RSB1
B14	GND
B15	IO98RSB1
B16	IO95RSB1
B17	GND
B18	IO87RSB1
B19	IO81RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO62RSB0

QN132	
Pin Number	A3P125 Function
B25	GND
B26	NC
B27	GCB2/IO58RSB0
B28	GND
B29	GCB0/IO54RSB0
B30	GCC1/IO51RSB0
B31	GND
B32	GBB2/IO43RSB0
B33	VMV0
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO67RSB1
C2	IO132RSB1
C3	VCC
C4	GFB1/IO124RSB1
C5	GFA0/IO122RSB1
C6	GFA2/IO120RSB1
C7	IO117RSB1
C8	VCCIB1
C9	GEA1/IO108RSB1
C10	GNDQ
C11	GEA2/IO106RSB1
C12	IO103RSB1
C13	VCCIB1
C14	IO97RSB1
C15	IO93RSB1
C16	IO89RSB1

FG144



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.actel.com/products/solutions/package/docs.aspx.

FG256	
Pin Number	A3P1000 Function
G13	GCC1/IO91PPB1
G14	IO90NPB1
G15	IO88PDB1
G16	IO88NDB1
H1	GFB0/IO208NPB3
H2	GFA0/IO207NDB3
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1

FG256	
Pin Number	A3P1000 Function
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3

FG256	
Pin Number	A3P1000 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the Automotive ProASIC3 datasheet.

Revision	Changes	Page
Revision 5 (January 2013)	The "Automotive ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43222).	1-III
	Added a note to Table 2-2 • Recommended Operating Conditions (SAR 43675): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in Table 2-116 • Automotive ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42560).	2-80
	Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 4 (September 2012)	The "Specifying I/O States During Programming" section is new (SAR 34691).	1-6
	Table 2-2 • Recommended Operating Conditions was revised to change VPUMP values for programming mode from "3.0 to 3.6" to "3.15 to 3.45" (SAR 34703).	2-2
	Maximum values for VIL and VIH were corrected in LVPECL Table 2-86 • Minimum and Maximum DC Input and Output Levels (SAR 37693).	2-52
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in the following tables (SAR 34804): Table 2-99 • Input DDR Propagation Delays (T_J = 135°C) Table 2-100 • Input DDR Propagation Delays (T_J = 115°C) Table 2-102 • Output DDR Propagation Delays (T_J = 135°C) Table 2-103 • Output DDR Propagation Delays (T_J = 115°C)	2-64 to 2-68
	Added values for minimum pulse width and removed the FRMAX row from Table 2-108 through Table 2-115 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 36966).	2-76
	SRAM collision data was added to Table 2-117 • RAM4K9 through Table 2-120 • RAM512X18. Maximum frequency, F_{MAX}, was updated in Table 2-118 • RAM512X18 (SAR 40859).	2-86 to 2-89
	The "VMVx I/O Supply Voltage (quiet)" section was revised. The sentence, "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" was replaced with, "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38323). VMV pins must be connected to the corresponding VCCI pins, as noted in the "VMVx I/O Supply Voltage (quiet)" section, for an ESD enhancement.	3-1
	Libero Integrated Design Environment (IDE) was changed to Libero Systeom-on-Chip (SoC) throughout the document (SAR 40266).	N/A
Revision 3 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1